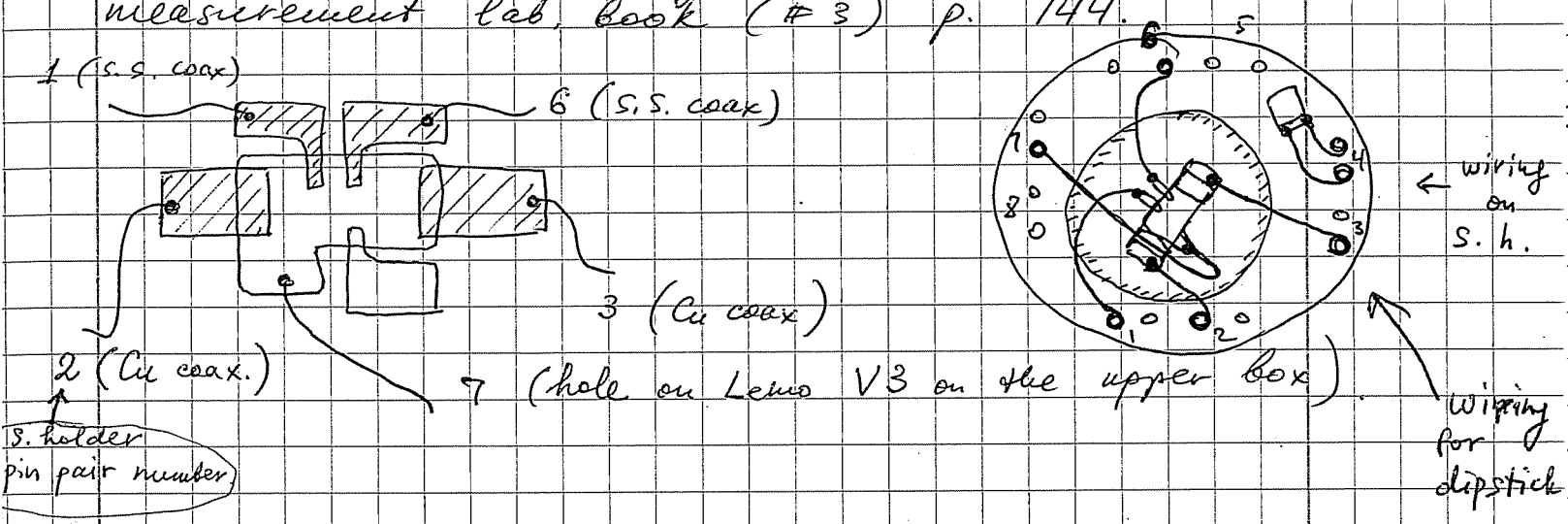


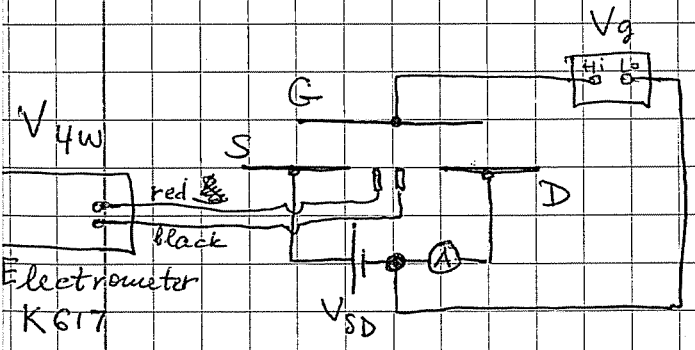
03/25/03. Measurements of another 4-probe MOSFET on Rubrene. (Sample made 03.24.03, see the deposition lab. book)

For current wiring of the deepstick see previous measurement lab. book (#3) p. 144.



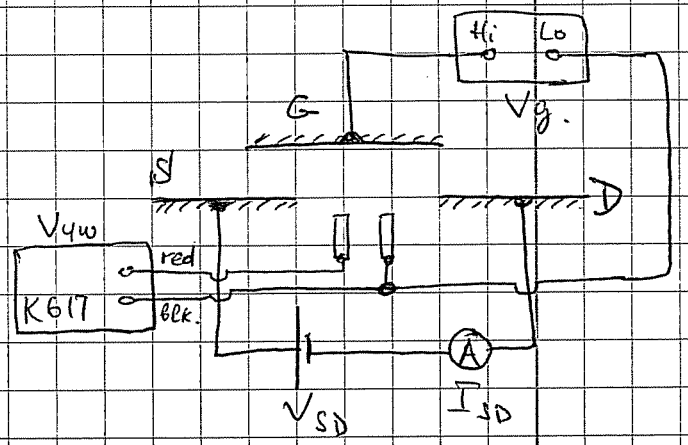
Two schemes were used to measure this 4 probe MosFET.

(1) Standard.



$V_g$  is applied rel. Drain and both  $V_{4w}$  contacts are floating and conn. to Electrometer K617.

(2)  $V_g$  is appl. rel. one of the  $V_{4w}$  contacts.



Calculating  $\mu$  from 4-probe measurements:

$$G_{\square}^{4w} = \frac{I_{SD}}{V_{4w}} \cdot \frac{D}{W} = \mu C_i (V_g + V_{SD})$$

